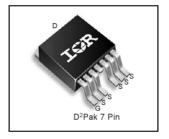
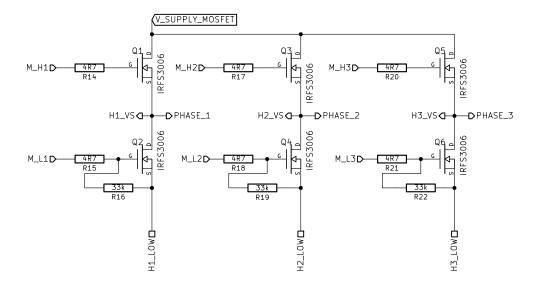


HEXFET® Power MOSFET

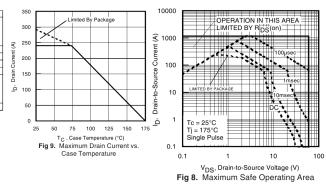


V _{DSS}	60V
R _{DS(on)} typ.	1.5m Ω
max.	$2.1 m\Omega$
I _{D (Silicon Limited)}	293A①
I _{D (Package Limited)}	240A





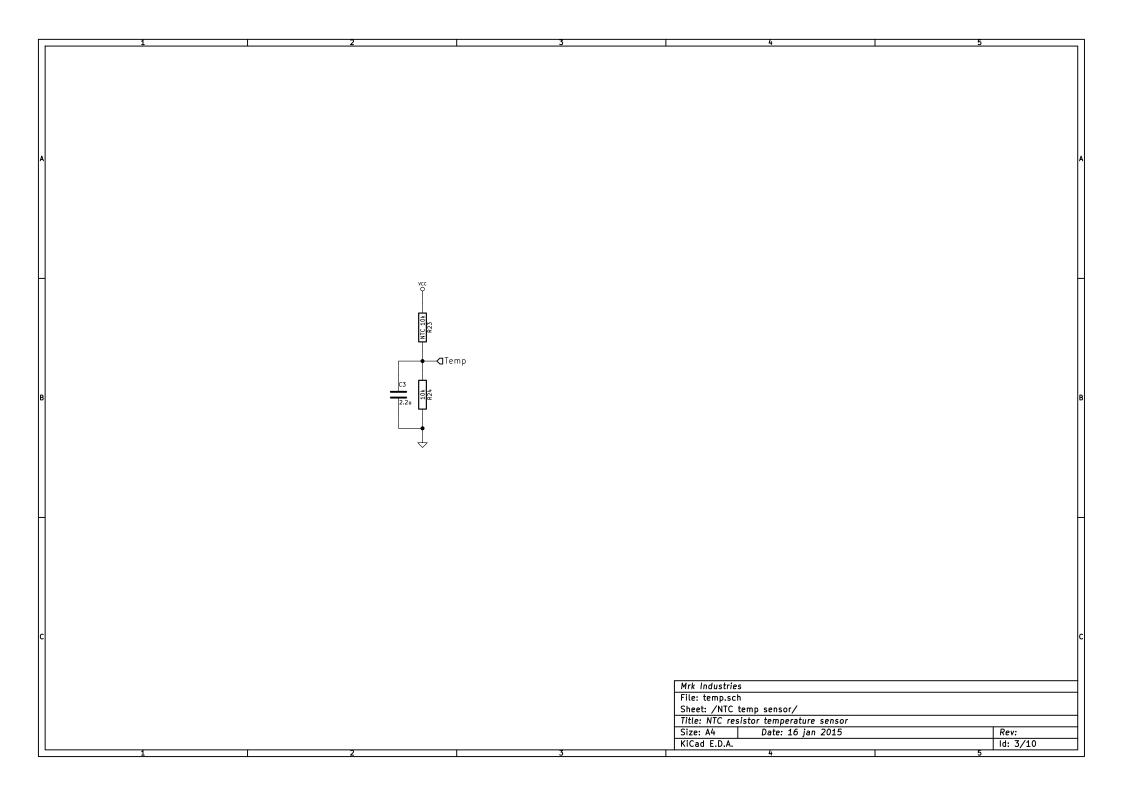
Absolute Maximum Ratings				
Symbol	Parameter	Max.	Units	
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V (Silicon Limited)	293®		
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V (Silicon Limited)	207 ①	Ι	
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V (Package Limited)	240	_ ^	
I _{DM}	Pulsed Drain Current ②	1172		
P _D @T _C = 25°C	Maximum Power Dissipation	375	W	
	Linear Derating Factor	2.5	W/°C	
V _{GS}	Gate-to-Source Voltage	± 20	٧	
dv/dt	Peak Diode Recovery @	11	V/ns	
T,	Operating Junction and	-55 to + 175		
T _{STG}	Storage Temperature Range		°C	
	Soldering Temperature, for 10 seconds	300	1 "	
	(1.6mm from case)			
	Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)		

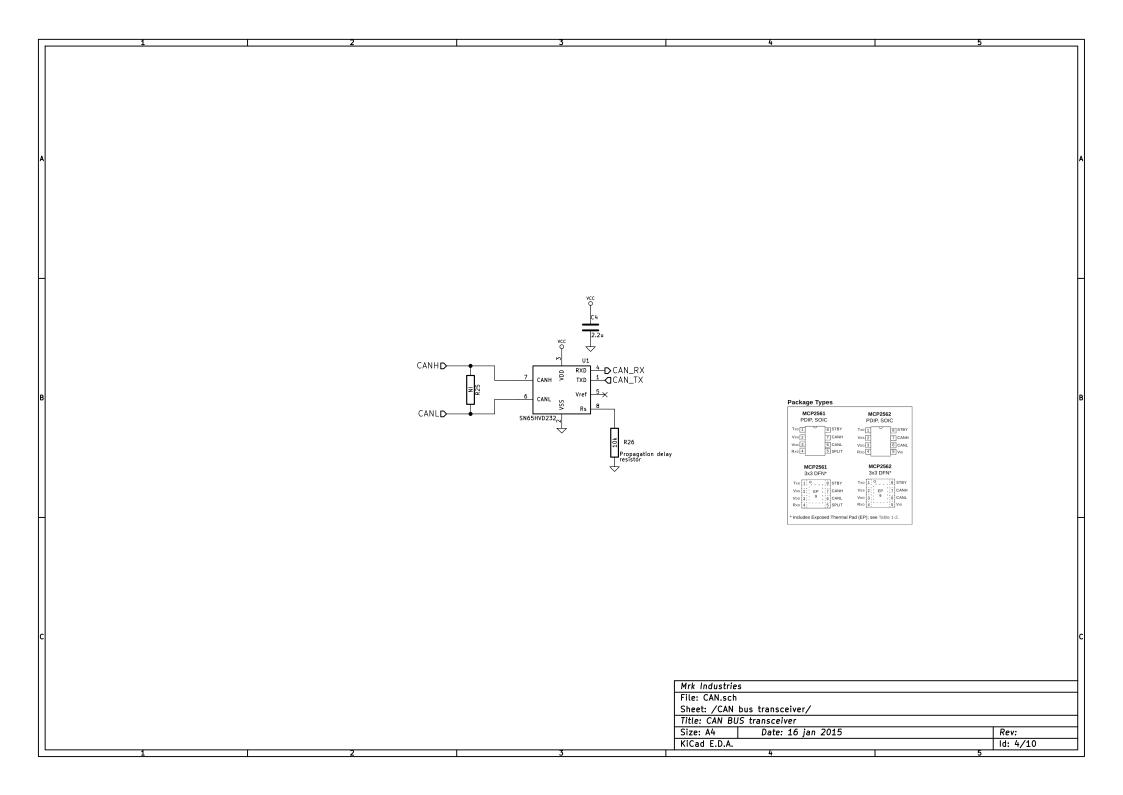


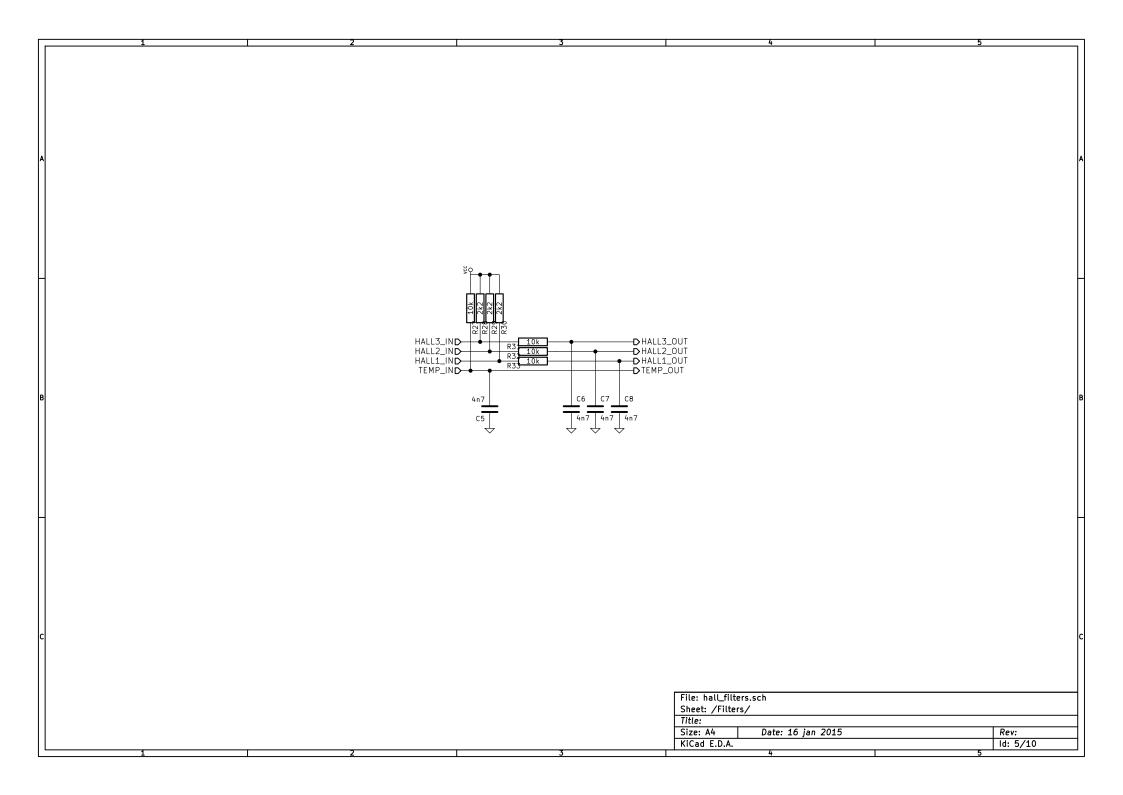
Benjamin Vedder			
File: mosfets.sch			
Sheet: /Power MOSFETS/			
Title: BLDC Driver 4.6			
Size: A4	Date: 16 jan 2015	Rev: 4.6	
KiCad E.D.A.		ld: 2/10	

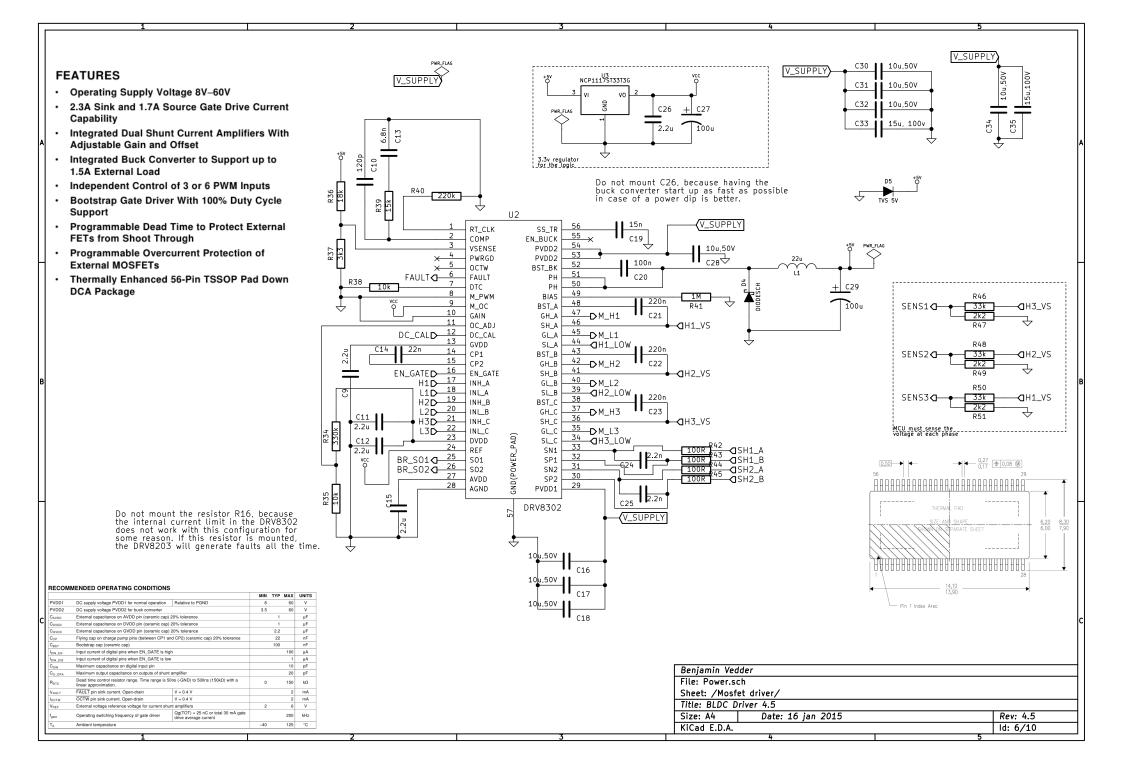
SEATING PLANE

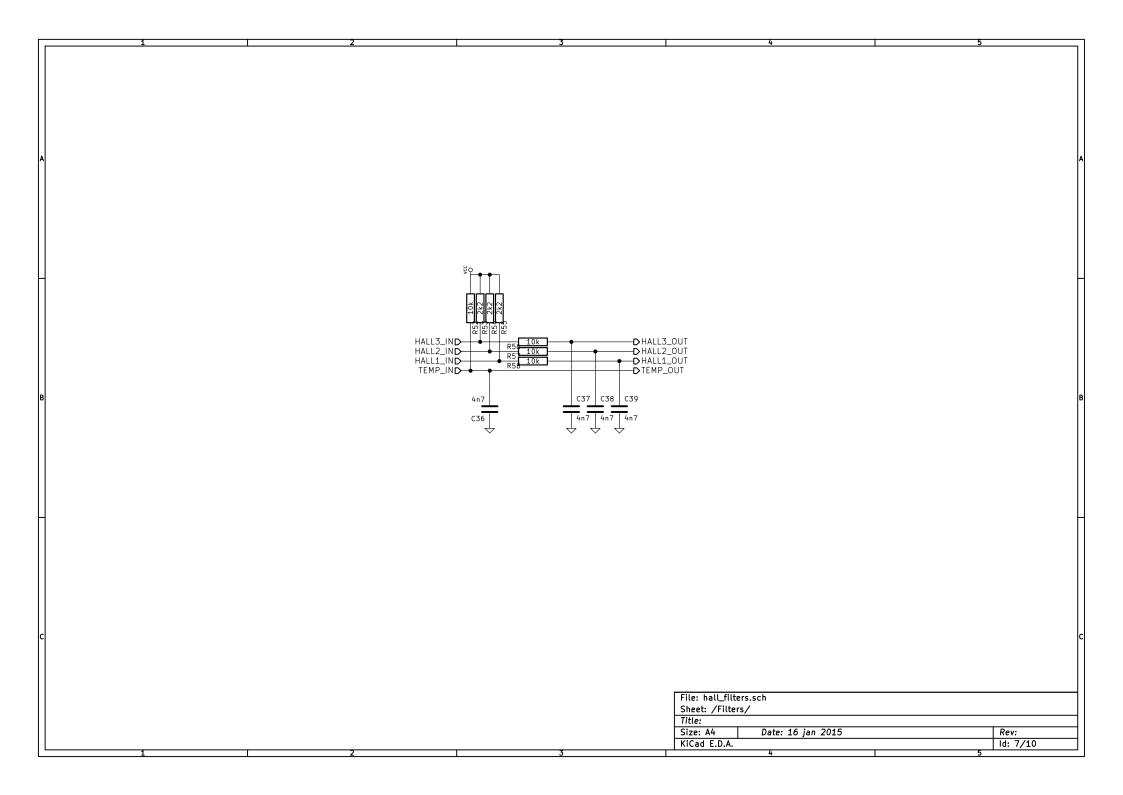
c → -// ±.004⊗B







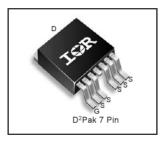


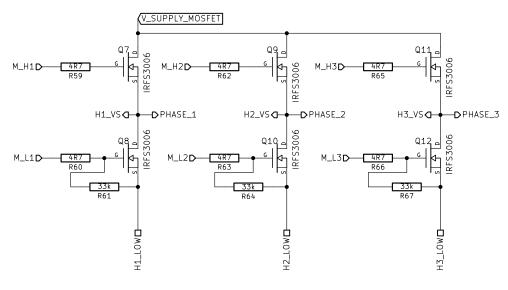


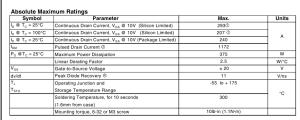
HEXFET® Power MOSFET

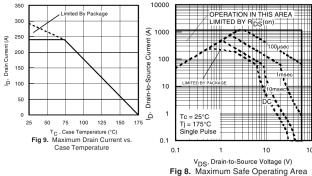


V _{DSS}	60V
R _{DS(on)} typ.	1.5m Ω
max.	$2.1 m\Omega$
I _{D (Silicon Limited)}	293A①
I _{D (Package Limited)}	240A



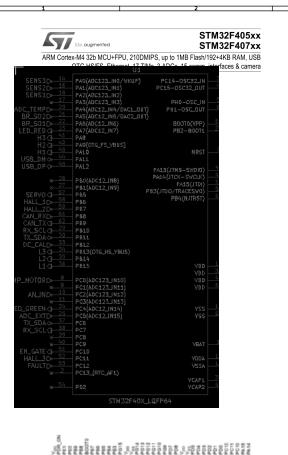






DETAIL A SEATING PLANE
LEAD TIP

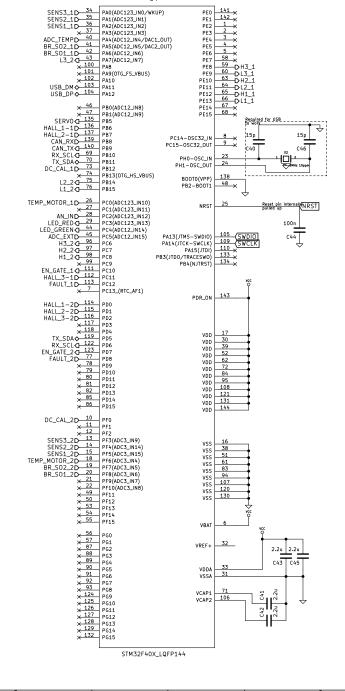
Benjamin Vedder			
File: mosfets.sch			
Sheet: /Power MOSFETS/			
Title: BLDC Driver 4.6			
Size: A4	Date: 16 jan 2015		Rev: 4.6
KiCad E.D.A.			ld: 8/10



105 PA11

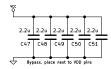
100 D PA 10 100 D PA 10 101 D PA 9 100 D PA 8 99 D PC9 98 D PC8 97 D PC7

PER CONTROL OF PER CO



U4

PE0 141 × PE1 142 × PE2 1 ×





Programming / Debug connector

Benjamin Vedder File: STM32F4 144LQFP.sch Sheet: /MCU/ Title: BLDC Driver 4.6 Date: 16 jan 2015 Size: A3 Rev: 4.6 KiCad E.D.A ld: 9/10

